TO-92 Plastic-Encapsulate Transistors

2N5770 TRANSISTOR（ NPN ）

FEATURES

Power dissipation

P_{CM}: 0.350 W（Tamb=25℃）

Collector current

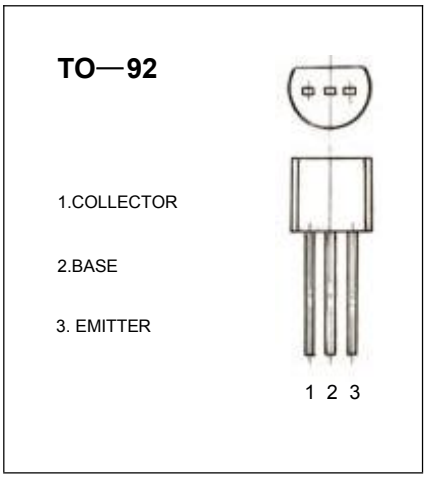
I_{CM}: 0.05 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃



ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic=1.0μA, I_E=0	30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic=3mA，I_B=0	15			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=10μA，I_C=0	4.5			V
Collector cut-off current	I_{CBO}	V_{CB}=15 V , I_E=0			10	μA
Collector cut-off current	I_{CBO}	V_{EB}= 15 V,I_C=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V, I_C=0mA			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=2V, I_C=0mA			1	μA
DC current gain	H_{FE}（1）	V_{CE}=1V, I_C=3mA	20			
DC current gain	H_{FE}（2）	V_{CE}=10V, I_C=8mA	50		200	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=1mA			0.4	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=10mA, I_B=1mA			1	V

CLASSIFICATION OF HFE

Rank	1	2	3
Range	20-80	80-150	150-200